4V Drive Nch MOSFET

RSF015N06FRA

Datasheet

AEC-Q101 Qualified

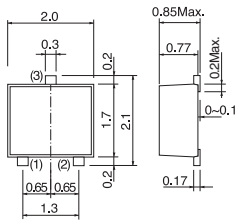
●Structure
Silicon N-channel MOSFET

●Features
1) Built-in G-S Protection Diode.
2) Small Surface Mount Package (TUMT3).
3) Low voltage drive. (4V)

●Application
Switching

●Dimensions (Unit : mm)

TUMT3

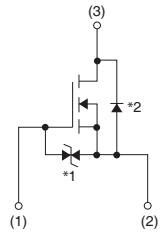


Abbreviated symbol : PX

●Packaging specifications

Type	Package	Taping
	Code	TL
	Quantity (pcs)	3000
RSF015N06FRA		O

●Inner circuit



(1) Gate
(2) Source
(3) Drain

∗1 ESD PROTECTION DIODE
∗2 BODY DIODE

●Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	60	V
Gate-source voltage		V_{GSS} *1	±20	V
Drain current	Continuous	I_D	±1.5	A
	Pulsed	I_{DP} *1	±6.0	A
Source current (Body Diode)	Continuous	I_S	0.6	A
	Pulsed	I_{SP} *1	6.0	A
Power dissipation		P_D *2	0.8	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	−55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1%

*2 Mounted on a ceramic board.

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	156	°C / W

*Mounted on a ceramic board.

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●**Electrical characteristics** (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	±10	μA	V_{GS}=±20V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)DSS}$	60	-	-	V	I_D=1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	V_{DS}=60V, V_{GS}=0V
Gate threshold voltage	$V_{GS\ (th)}$	1.0	-	2.5	V	V_{DS}=10V, I_D=1mA
Static drain-source on-state resistance	$R_{DS\ (on)}$ *	-	210	290	mΩ	I_D=1.5A, V_{GS}=10V
		-	240	330		I_D=1.5A, V_{GS}=4.5V
		-	255	350		I_D=1.5A, V_{GS}=4.0V
Forward transfer admittance	$\|Y_{fs}\|$*	1.0	-	-	S	I_D=1.5A, V_{DS}=10V
Input capacitance	C_{iss}	-	110	-	pF	V_{DS}=10V
Output capacitance	C_{oss}	-	28	-	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	-	12	-	pF	f=1MHz
Turn-on delay time	$t_{d(on)}$*	-	6	-	ns	I_D=0.7A, V_{DD}≒30V
Rise time	t_r *	-	9	-	ns	V_{GS}=10V
Turn-off delay time	$t_{d(off)}$*	-	15	-	ns	R_L=42.8Ω
Fall time	t_f *	-	10	-	ns	R_G=10Ω
Total gate charge	Q_g *	-	2.0	-	nC	I_D=1.5A
Gate-source charge	Q_{gs} *	-	0.8	-	nC	V_{DD}≒30V
Gate-drain charge	Q_{gd} *	-	0.5	-	nC	V_{GS}=5V

*Pulsed

●**Body diode characteristics** (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD}*	-	-	1.2	V	I_s=1.5A, V_{GS}=0V

*Pulsed

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●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics(Ⅰ)

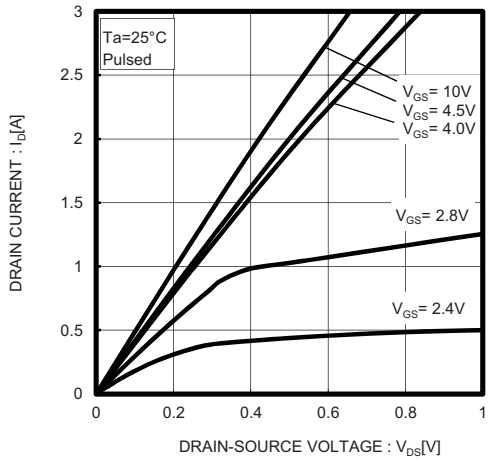


Fig.2 Typical Output Characteristics(Ⅱ)

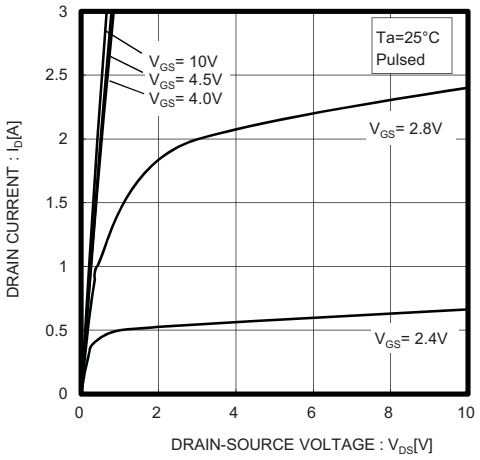


Fig.3 Typical Transfer Characteristics

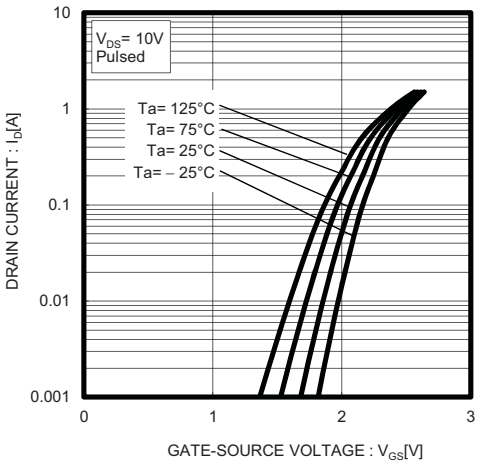


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(Ⅰ)

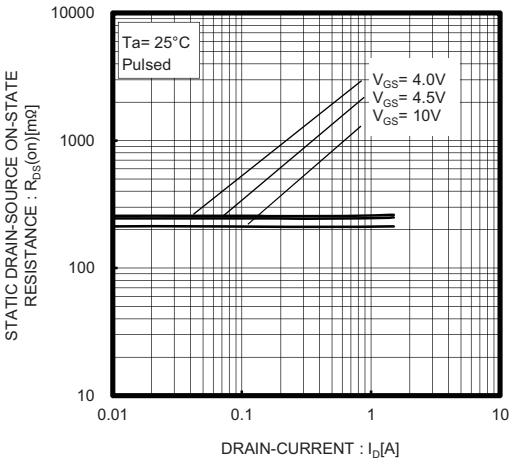


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(Ⅱ)

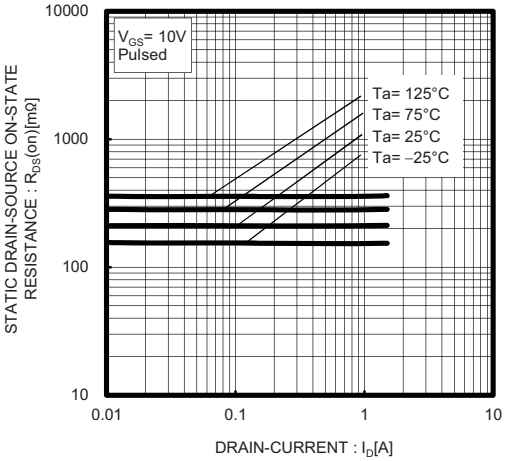
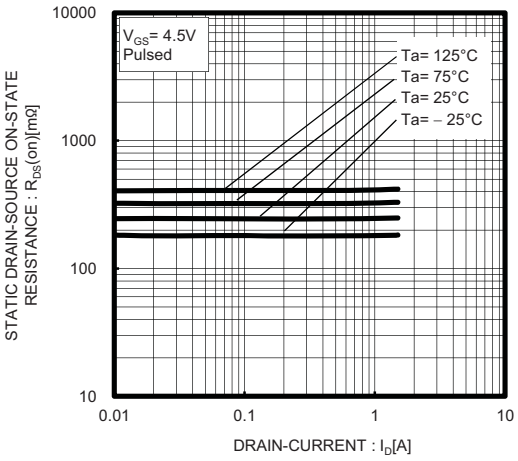


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(Ⅲ)



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Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(Ⅳ)

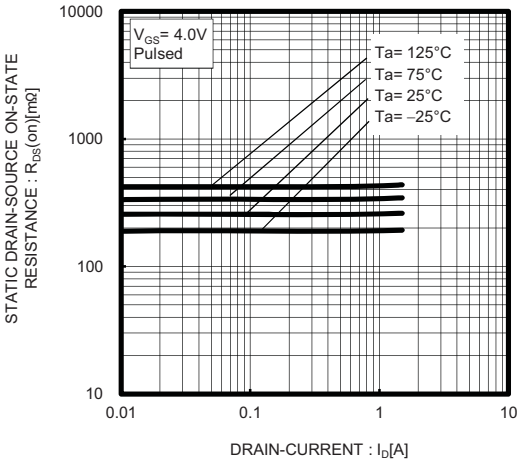


Fig.8 Forward Transfer Admittance vs. Drain Current

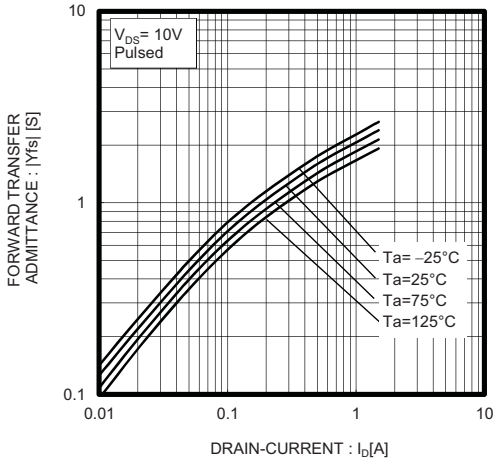


Fig.9 Source Current vs. Sourse-Drain Voltage

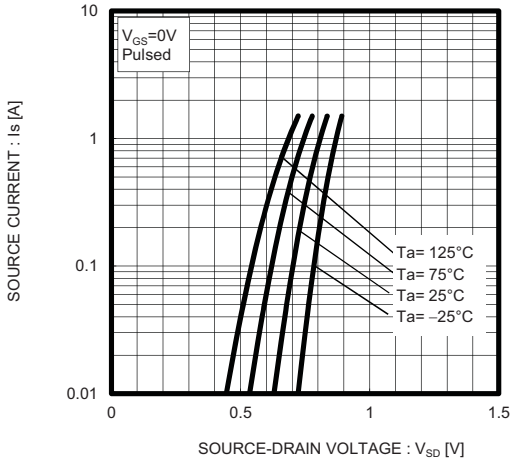


Fig.10 Static Drain-Source On-State Resistance vs. Gate Source Voltage

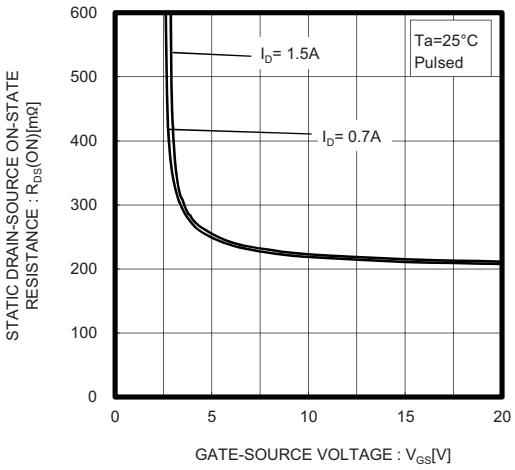


Fig.11 Switching Characteristics

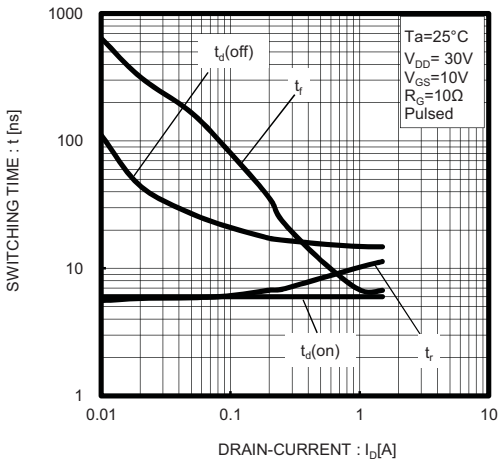
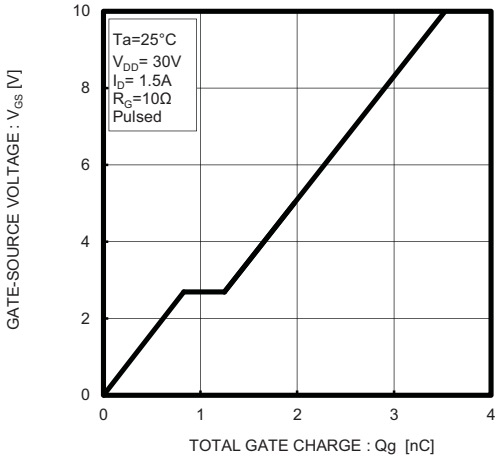


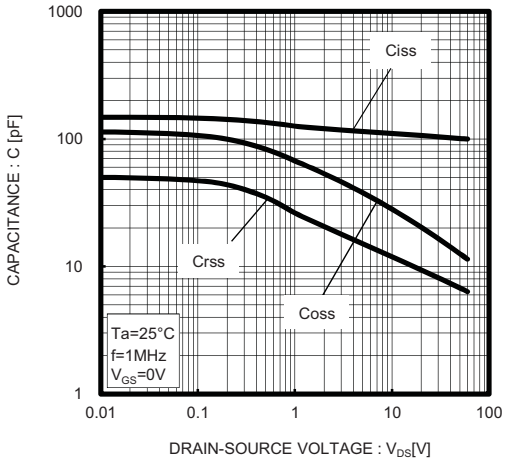
Fig.12 Dynamic Input Characteristics



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Fig.13 Typical Capacitance vs. Drain-Source Voltage



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●Measurement circuits

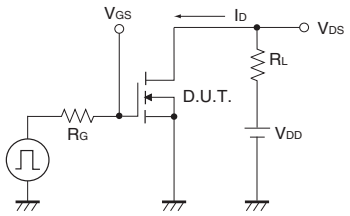


Fig.1-1 Switching Time Measurement Circuit

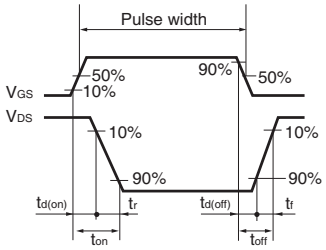


Fig.1-2 Switching Waveforms

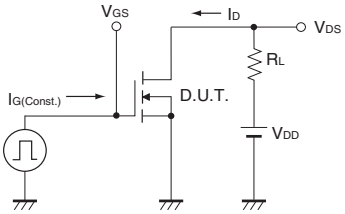


Fig.2-1 Gate Charge Measurement Circuit

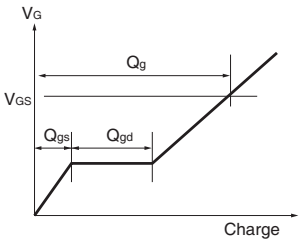


Fig.2-2 Gate Charge Waveform

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Distribution Inventory

Part Number	RSF015N06FRA
Package	TUMT3
Unit Quantity	3000
Minimum Package Quantity	3000
Packing Type	Taping
Constitution Materials List	inquiry
RoHS	Yes

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